Fig. 1

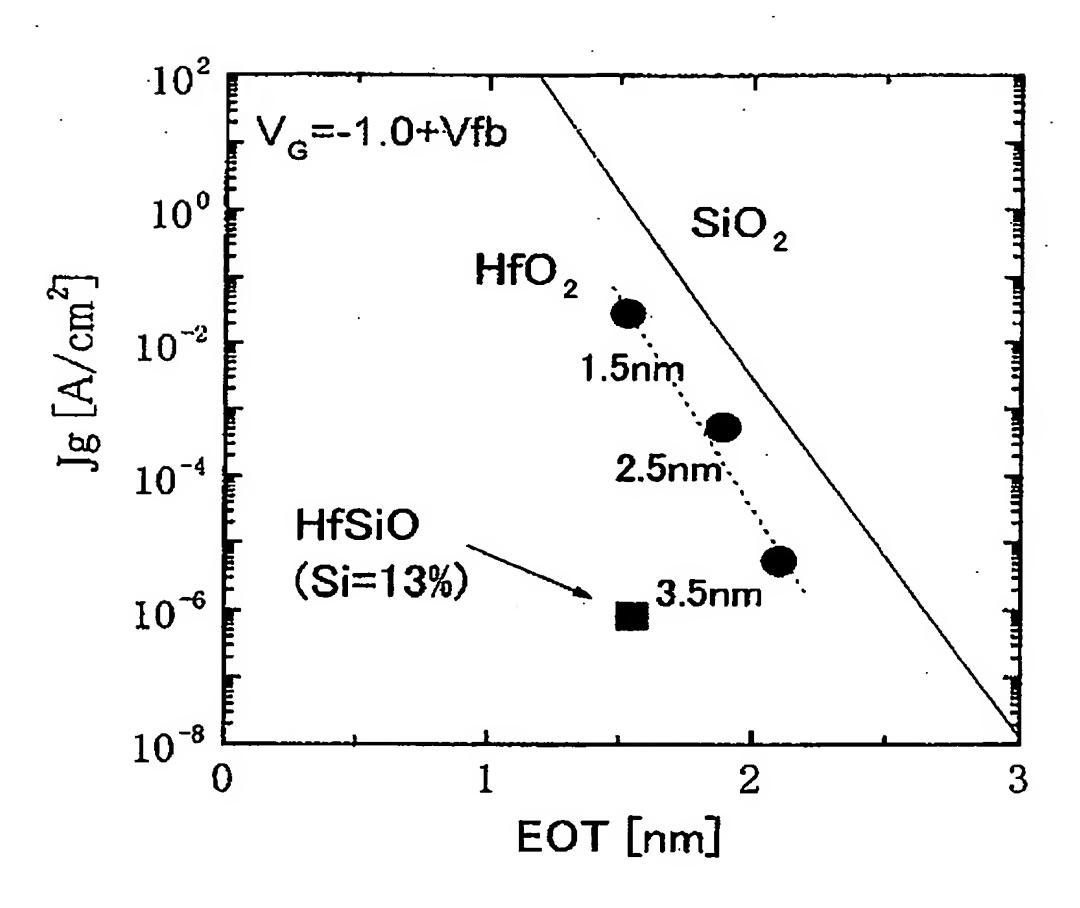
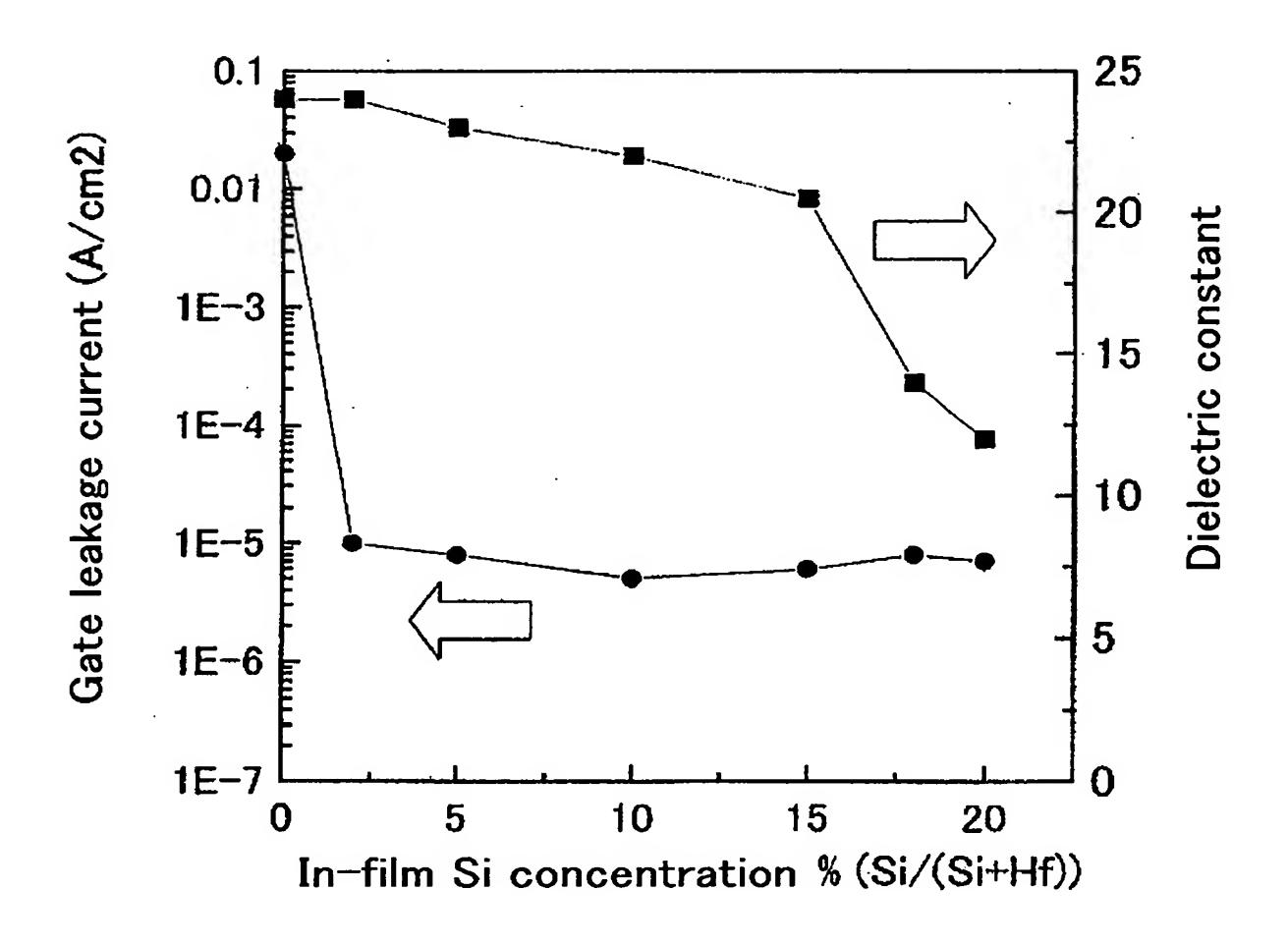


Fig. 2



ventor(s): 10ru 1A15UMI, of Appl. No.: Unassigned

Fig. 3

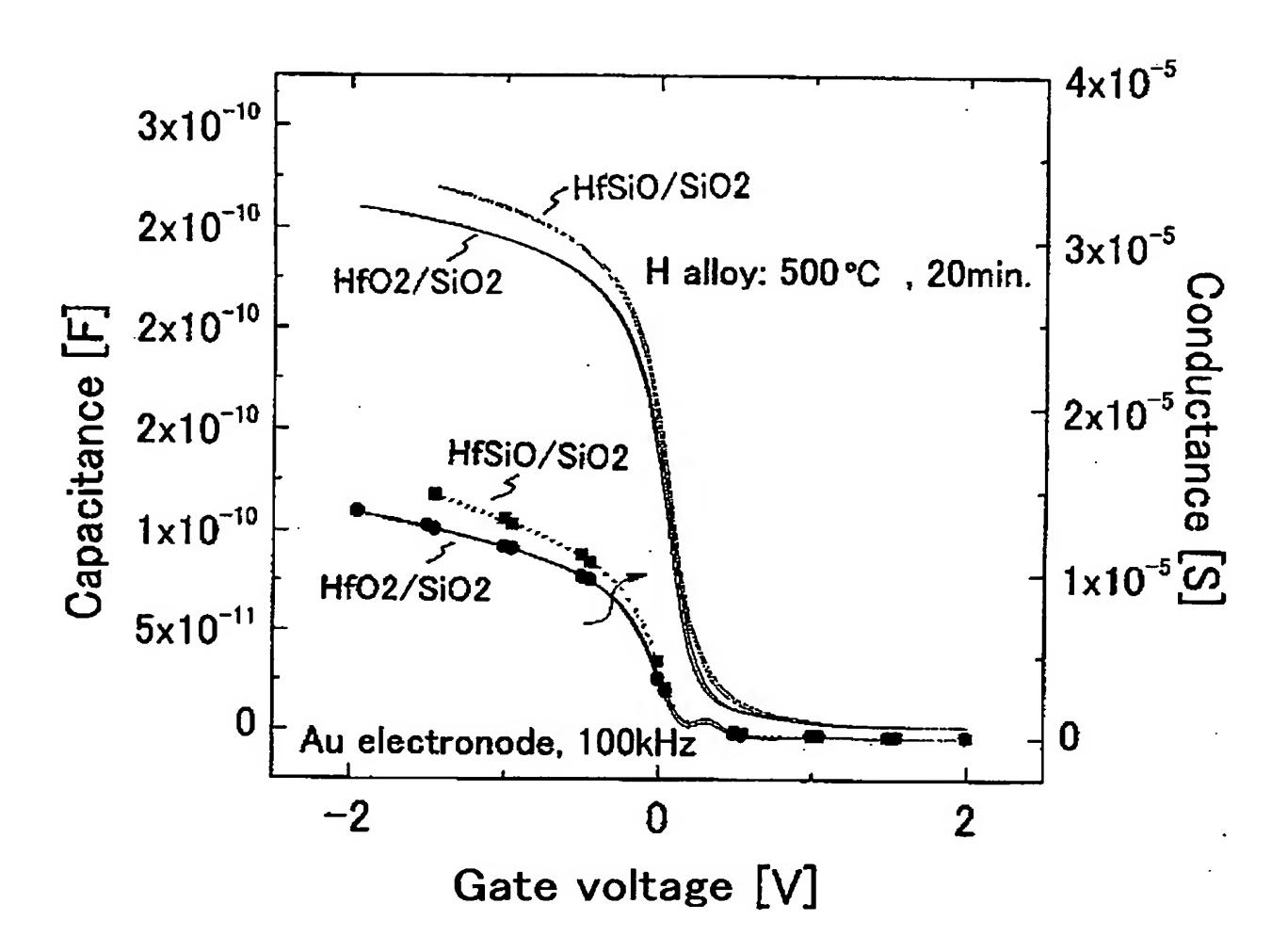


Fig. 4

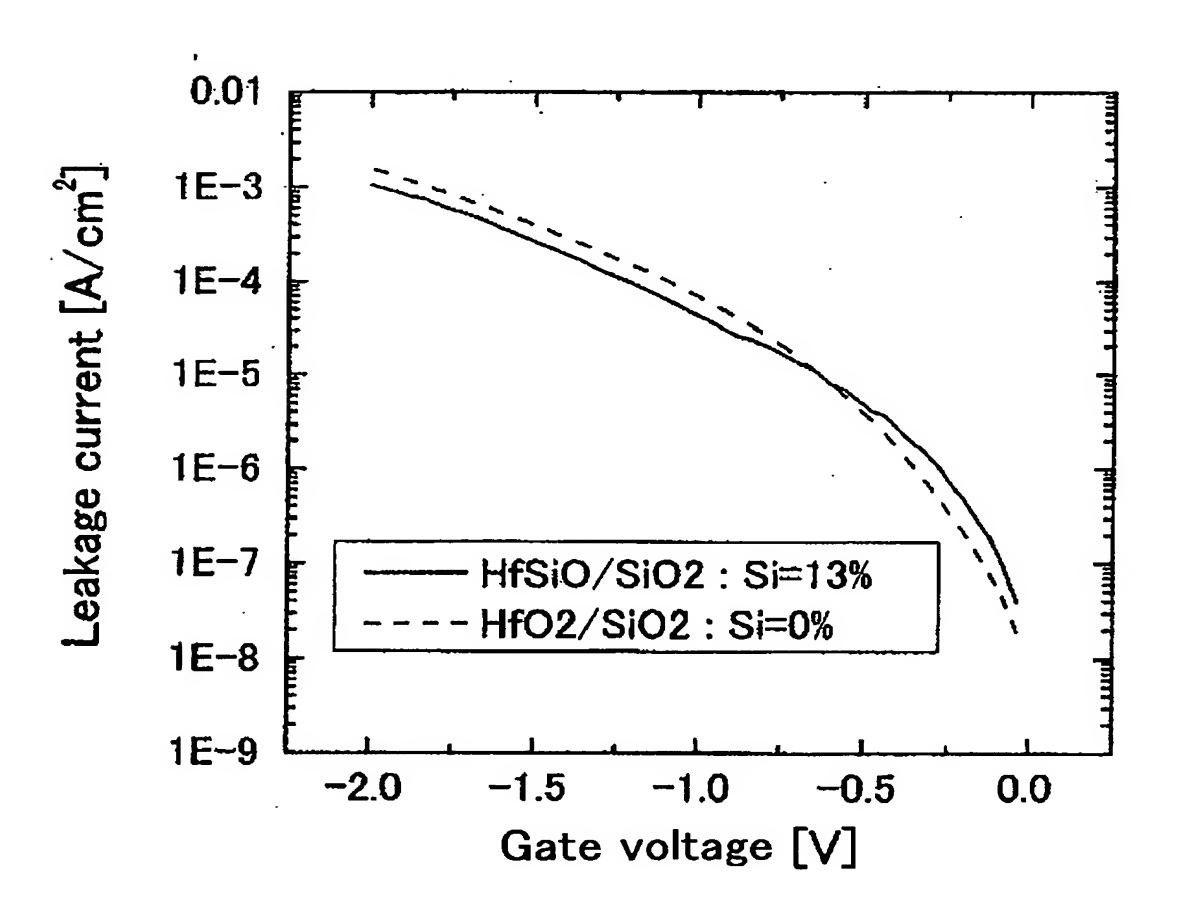
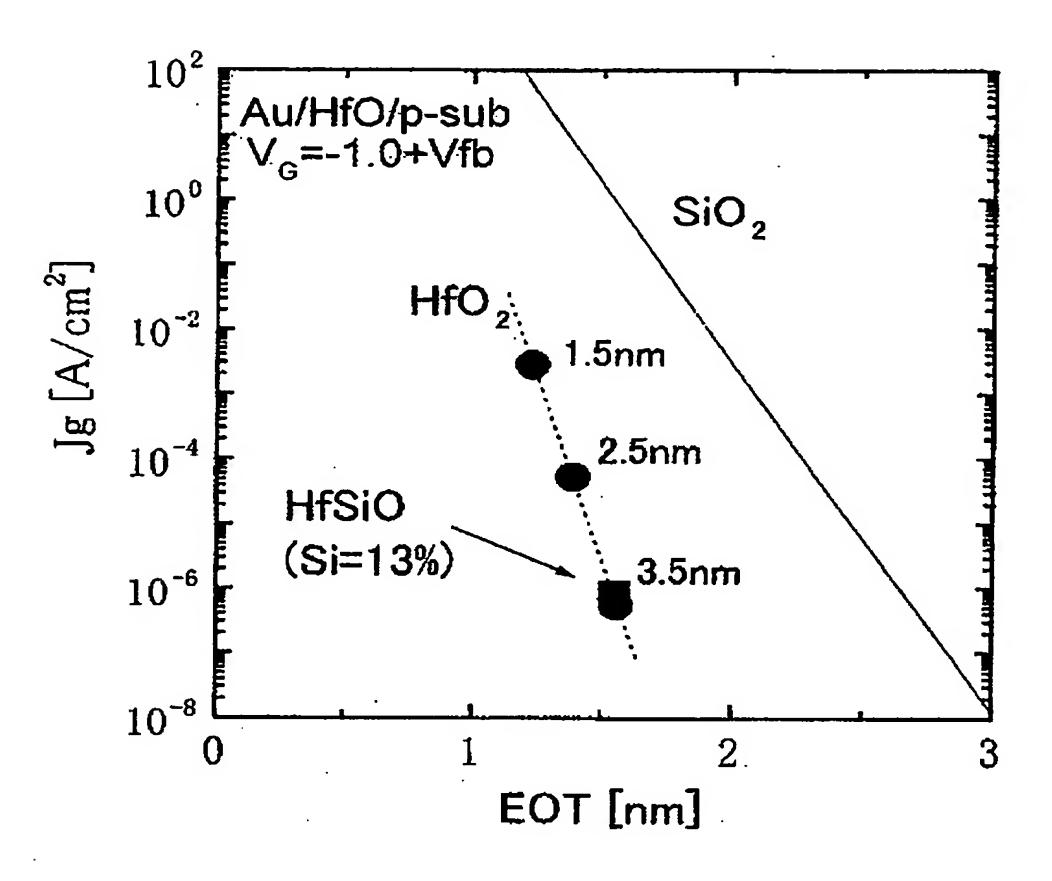
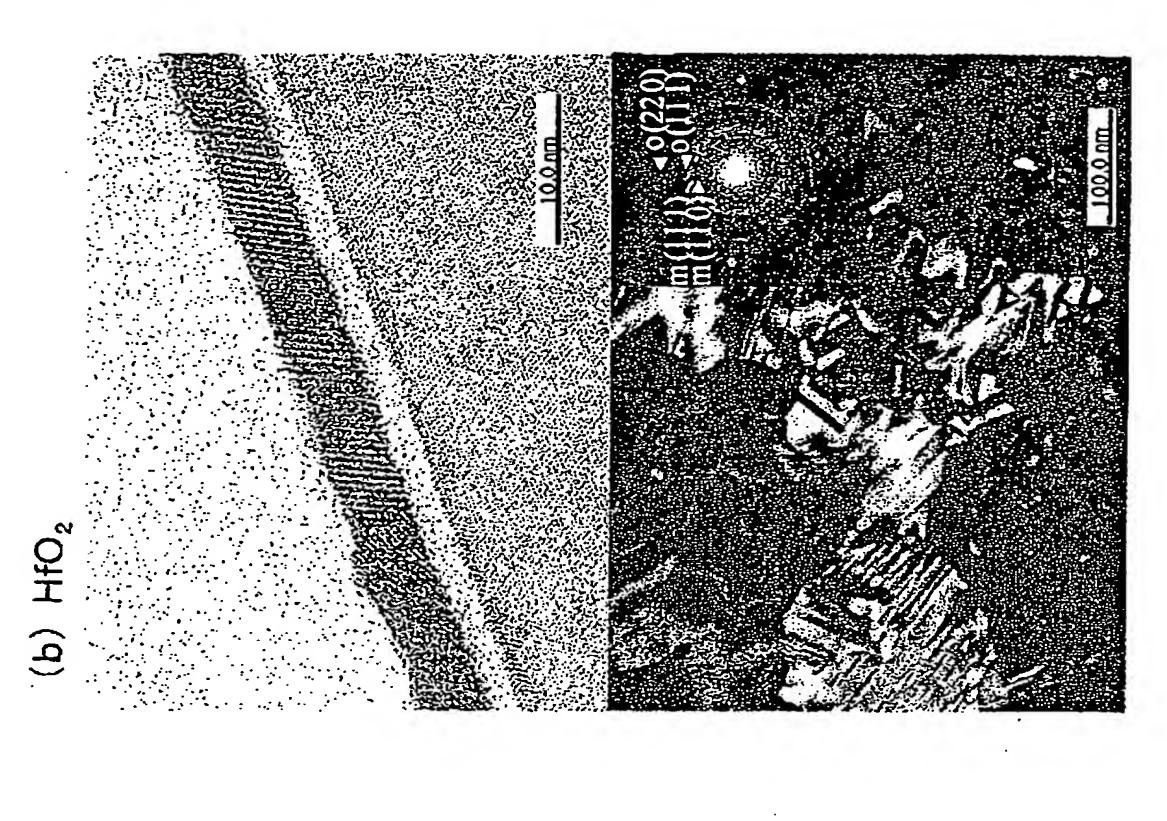
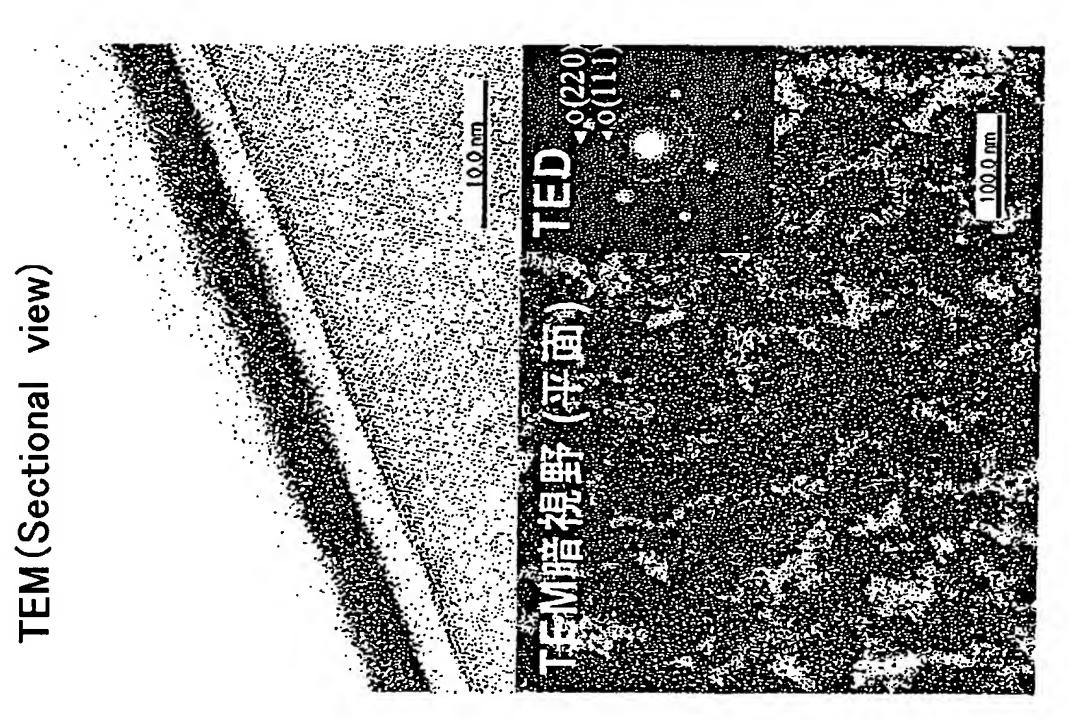


Fig. 5



(a) HfSiO



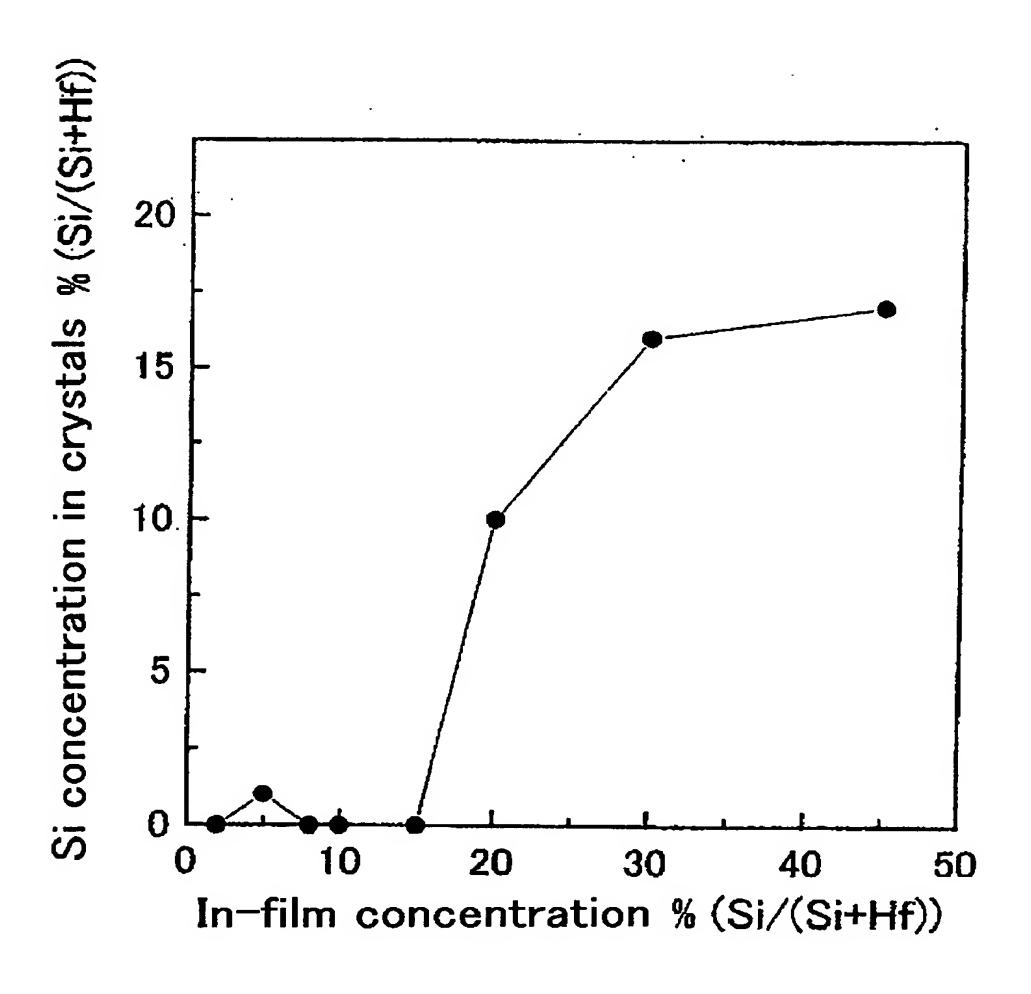


TEM Dark Field (Top plan view)

Title: SEMICONDUCTOR DEVICE HAVING A
MIS-TYPE FET, AND METHODS FOR
MANUFACTURING THE SAME AND FORMING
A METAL OXIDE FILM

Inventor(s): Toru TATSUMI, et al. Appl. No.: Unassigned

Fig. 7



Title: SEMICONDUCTOR DEVICE HAVING A MIS-TYPE FET, AND METHODS FOR : MANUFACTURING THE SAME AND FORMING A METAL OXIDE FILM Inventor(s): Toru TATSUMI, et al. Appl. No.: Unassigned Anneal after deposition for sintering the filr Oxidation by H<sub>2</sub>O Fig. 8 Form oxide film Absorb Hf am

Inventor(s): Toru TATSUMI, et al. Appl. No.: Unassigned

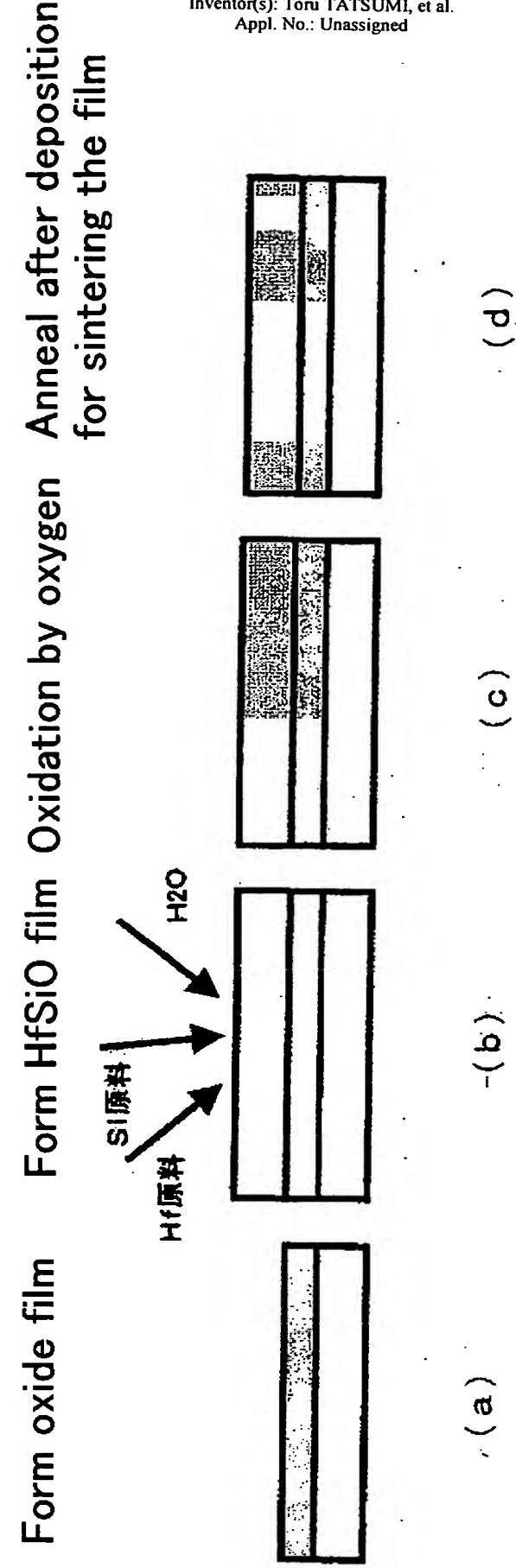


Fig. 10

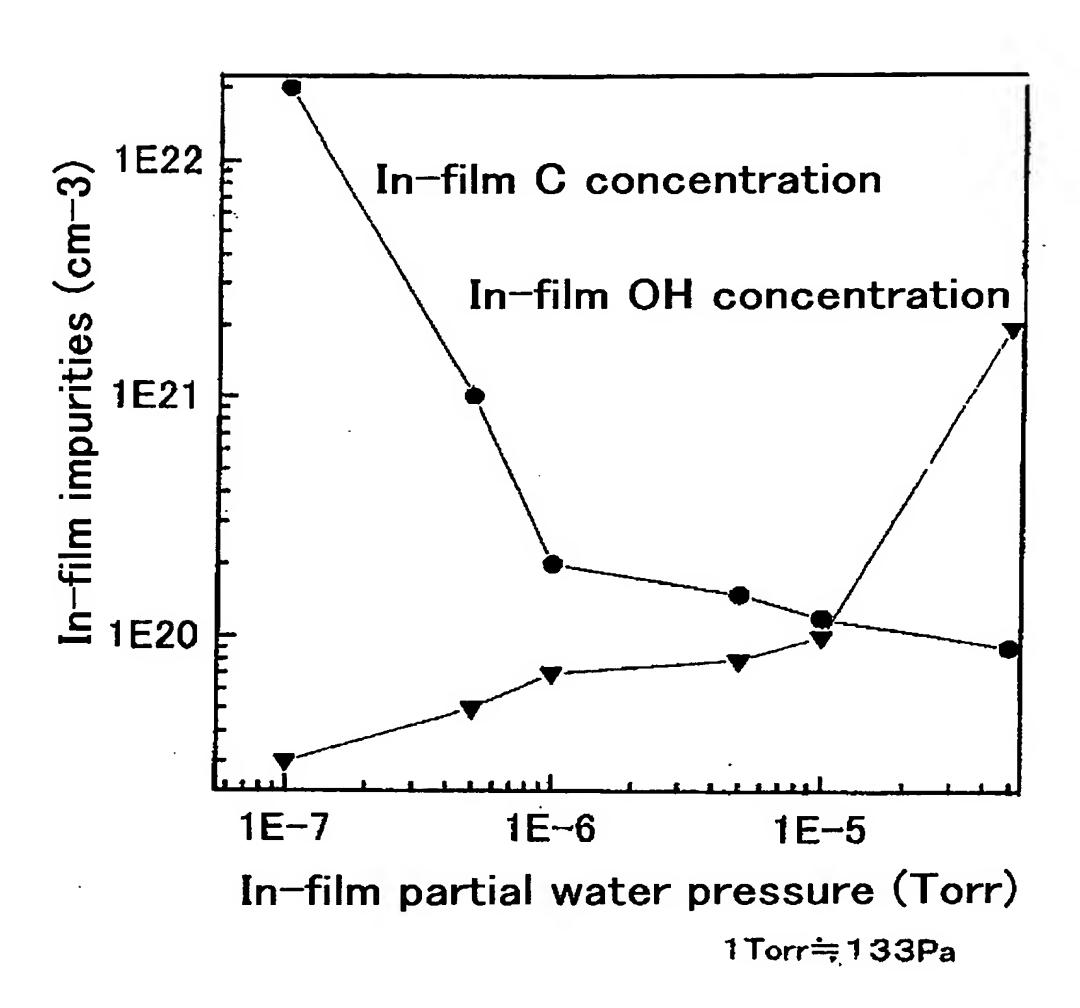


Fig. 11

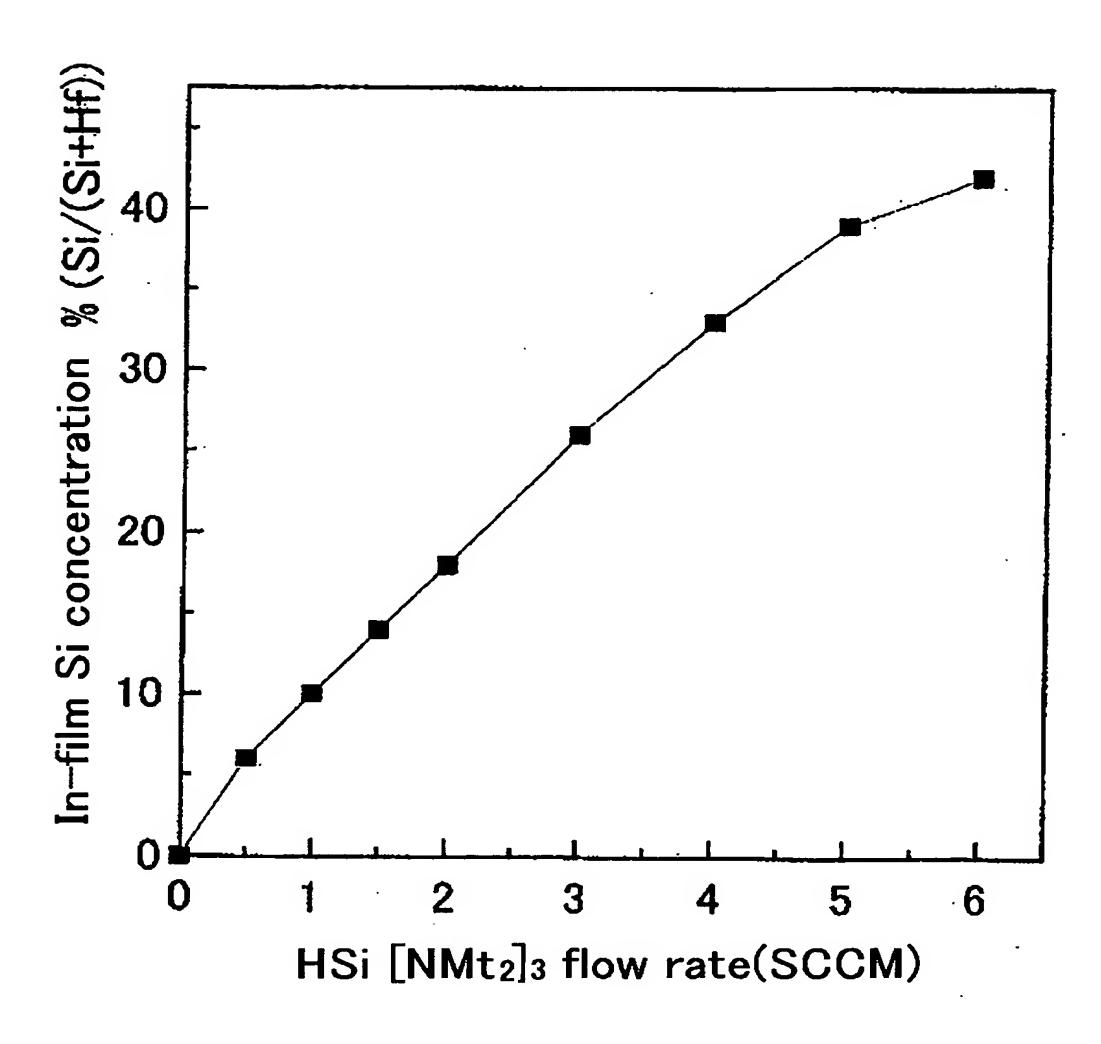


Fig. 12

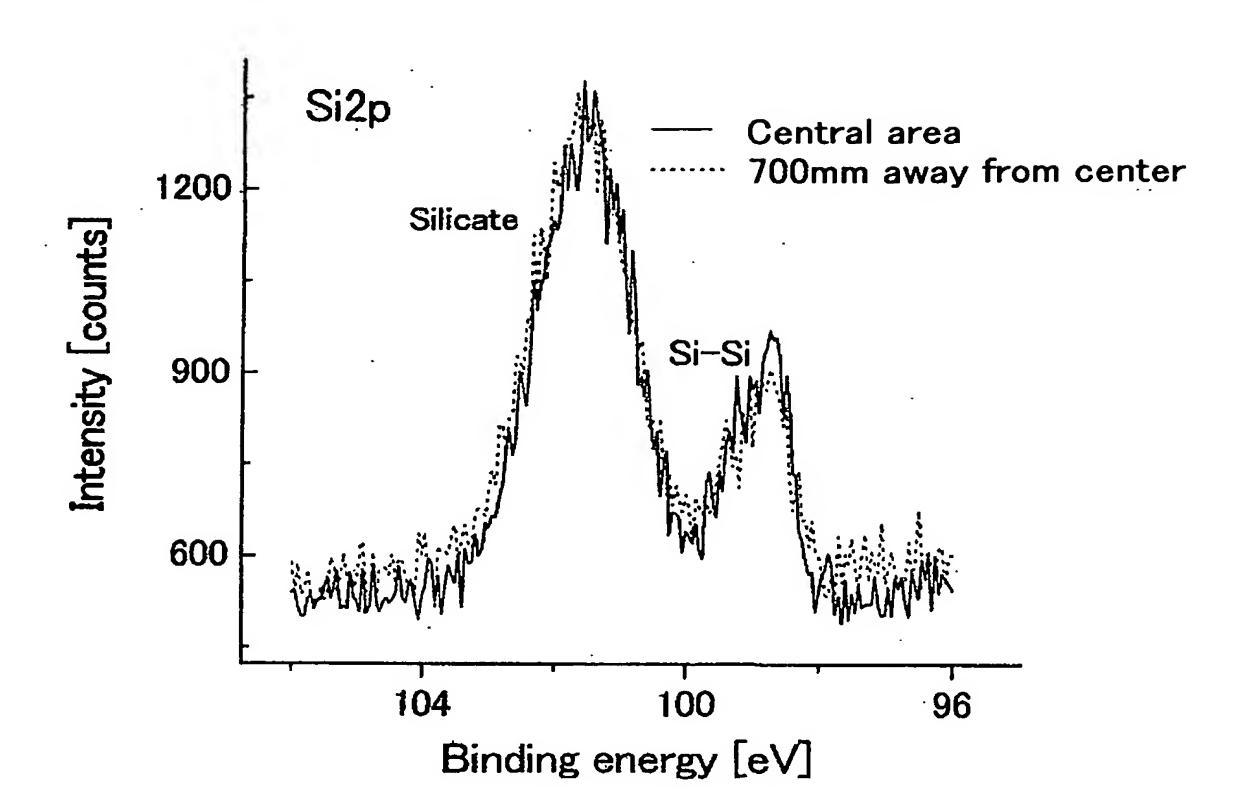
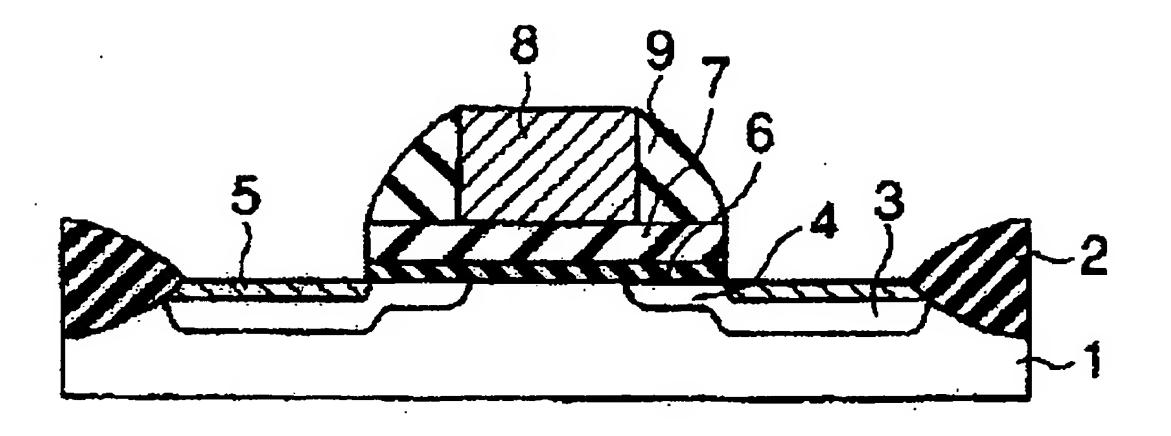


Fig. 13



3

Fig. 14

